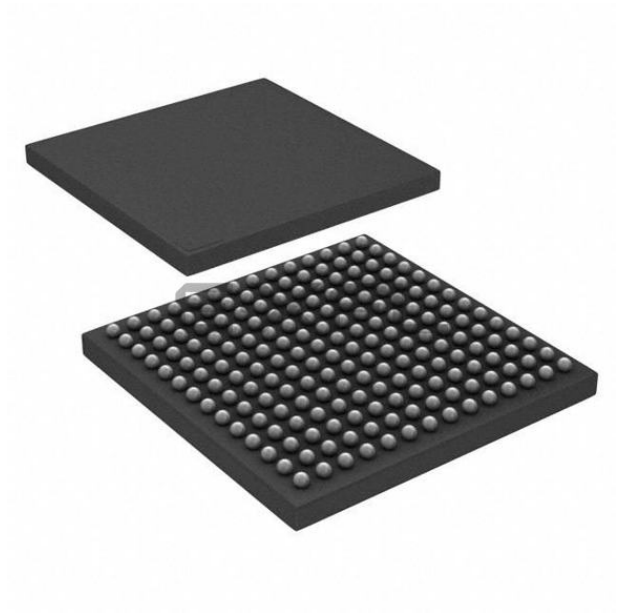

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	4075
Number of Logic Elements/Cells	52160
Total RAM Bits	2764800
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	196-LBGA, CSPBGA
Supplier Device Package	196-CSBGA (15x15)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s50-2ftgb196c

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HR I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 125°C	AC Voltage Undershoot	% of UI at –40°C to 125°C
V_{CCO} + 0.55	100	–0.40	100
		–0.45	61.7
		–0.50	25.8
		–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. The peak voltage of the overshoot or undershoot, and the duration above V_{CCO} + 0.20V or below GND – 0.20V, must not exceed the values in this table.

Table 5: **Typical Quiescent Supply Current(1)(2)(3)**

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XC7S6	36	36	36	36	36	32	mA
		XC7S15	36	36	36	36	36	32	mA
		XC7S25	48	48	48	48	48	43	mA
		XC7S50	95	95	95	95	95	59	mA
		XC7S75	148	148	148	148	148	134	mA
		XC7S100	148	148	148	148	148	134	mA
		XA7S6	N/A	36	N/A	36	36	N/A	mA
		XA7S15	N/A	36	N/A	36	36	N/A	mA
		XA7S25	N/A	48	N/A	48	48	N/A	mA
		XA7S50	N/A	95	N/A	95	95	N/A	mA
		XA7S75	N/A	148	N/A	148	148	N/A	mA
		XA7S100	N/A	148	N/A	148	148	N/A	mA

Table 5: **Typical Quiescent Supply Current[(1)(2)(3)] *(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCOQ}	Quiescent V_{CCO} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	1	1	1	1	1	1	mA
		XC7S75	4	4	4	4	4	4	mA
		XC7S100	4	4	4	4	4	4	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	1	N/A	1	1	N/A	mA
		XA7S75	N/A	4	N/A	4	4	N/A	mA
		XA7S100	N/A	4	N/A	4	4	N/A	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XC7S6	10	10	10	10	10	10	mA
		XC7S15	10	10	10	10	10	10	mA
		XC7S25	13	13	13	13	13	13	mA
		XC7S50	22	22	22	22	22	20	mA
		XC7S75	43	43	43	43	43	43	mA
		XC7S100	43	43	43	43	43	43	mA
		XA7S6	N/A	10	N/A	10	10	N/A	mA
		XA7S15	N/A	10	N/A	10	10	N/A	mA
		XA7S25	N/A	13	N/A	13	13	N/A	mA
		XA7S50	N/A	22	N/A	22	22	N/A	mA
		XA7S75	N/A	43	N/A	43	43	N/A	mA
		XA7S100	N/A	43	N/A	43	43	N/A	mA

Table 5: **Typical Quiescent Supply Current[(1)(2)(3)] *(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	2	2	2	2	2	1	mA
		XC7S75	9	9	9	9	9	8	mA
		XC7S100	9	9	9	9	9	8	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	2	N/A	2	2	N/A	mA
		XA7S75	N/A	9	N/A	9	9	N/A	mA
		XA7S100	N/A	9	N/A	9	9	N/A	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperature (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0 the following conditions apply.

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

There is no recommended sequence for supplies not discussed in this section.

Table 6 shows the minimum current, in addition to I_{CCQ} maximum, that is required by Spartan-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate current drain on these supplies.

Table 6: **Power-On Current**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
XC7S6	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S15	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S25	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S50	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S75	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S100	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S6	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S15	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S25	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S50	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S75	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S100	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA

Table 7: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}.		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}.		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}.		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}.		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$.	T_J = 125°C(1)	–	300	ms
		T_J = 100°C(1)	–	500	ms
		T_J = 85°C(1)	–	800	ms

Notes:

1. Based on 240,000 power cycles with a nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels**(1)(2)(3)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 6	Note 6
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 6	Note 6
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
HSTL_II_18_F	0.75	0.81	0.81	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_HSTL_I_F	0.76	0.83	0.83	1.30	1.56	1.56	1.33	1.57	1.57	ns
DIFF_HSTL_II_F	0.76	0.83	0.83	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_I_18_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_II_18_F	0.78	0.85	0.85	1.33	1.59	1.59	1.36	1.60	1.60	ns
LVCMOS33_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVCMOS33_S8	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVCMOS33_S12	1.34	1.41	1.41	3.21	3.46	3.46	3.24	3.48	3.48	ns
LVCMOS33_S16	1.34	1.41	1.41	3.52	3.77	3.77	3.55	3.79	3.79	ns
LVCMOS33_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVCMOS33_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS33_F12	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS33_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS25_S4	1.20	1.27	1.27	3.26	3.51	3.51	3.29	3.52	3.52	ns
LVCMOS25_S8	1.20	1.27	1.27	3.01	3.26	3.26	3.04	3.27	3.27	ns
LVCMOS25_S12	1.20	1.27	1.27	2.60	2.85	2.85	2.63	2.87	2.87	ns
LVCMOS25_S16	1.20	1.27	1.27	2.94	3.20	3.20	2.97	3.21	3.21	ns
LVCMOS25_F4	1.20	1.27	1.27	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS25_F8	1.20	1.27	1.27	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS25_F12	1.20	1.27	1.27	2.29	2.54	2.54	2.32	2.55	2.55	ns
LVCMOS25_F16	1.20	1.27	1.27	2.13	2.39	2.39	2.16	2.40	2.40	ns
LVCMOS18_S4	0.83	0.89	0.89	1.74	1.99	1.99	1.77	2.01	2.01	ns
LVCMOS18_S8	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S12	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S16	0.83	0.89	0.89	1.65	1.90	1.90	1.68	1.91	1.91	ns
LVCMOS18_S24	0.83	0.89	0.89	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS18_F4	0.83	0.89	0.89	1.57	1.82	1.82	1.60	1.84	1.84	ns
LVCMOS18_F8	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F12	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F16	0.83	0.89	0.89	1.52	1.77	1.77	1.55	1.79	1.79	ns
LVCMOS18_F24	0.83	0.89	0.89	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS15_S4	0.86	0.93	0.93	2.18	2.43	2.43	2.21	2.45	2.45	ns
LVCMOS15_S8	0.86	0.93	0.93	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS15_S12	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_S16	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_F4	0.86	0.93	0.93	1.97	2.23	2.23	2.00	2.24	2.24	ns

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVCMOS15_F8	0.86	0.93	0.93	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS15_F12	0.86	0.93	0.93	1.47	1.73	1.73	1.50	1.74	1.74	ns
LVCMOS15_F16	0.86	0.93	0.93	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS12_S4	0.95	1.02	1.02	2.69	2.95	2.95	2.72	2.96	2.96	ns
LVCMOS12_S8	0.95	1.02	1.02	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS12_S12	0.95	1.02	1.02	1.91	2.17	2.17	1.94	2.18	2.18	ns
LVCMOS12_F4	0.95	1.02	1.02	2.10	2.35	2.35	2.13	2.37	2.37	ns
LVCMOS12_F8	0.95	1.02	1.02	1.66	1.92	1.92	1.69	1.93	1.93	ns
LVCMOS12_F12	0.95	1.02	1.02	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_S	0.75	0.82	0.82	1.47	1.73	1.73	1.50	1.74	1.74	ns
SSTL15_S	0.68	0.75	0.75	1.43	1.68	1.68	1.46	1.69	1.69	ns
SSTL18_I_S	0.75	0.82	0.82	1.79	2.04	2.04	1.82	2.06	2.06	ns
SSTL18_II_S	0.75	0.82	0.82	1.43	1.68	1.68	1.46	1.70	1.70	ns
DIFF_SSTL135_S	0.76	0.83	0.83	1.47	1.73	1.73	1.50	1.74	1.74	ns
DIFF_SSTL15_S	0.76	0.83	0.83	1.43	1.68	1.68	1.46	1.69	1.69	ns
DIFF_SSTL18_I_S	0.79	0.86	0.86	1.80	2.06	2.06	1.83	2.07	2.07	ns
DIFF_SSTL18_II_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL15_F	0.68	0.75	0.75	1.19	1.45	1.45	1.22	1.46	1.46	ns
SSTL18_I_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL18_II_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL135_F	0.76	0.83	0.83	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL15_F	0.76	0.83	0.83	1.19	1.45	1.45	1.22	1.46	1.46	ns
DIFF_SSTL18_I_F	0.79	0.86	0.86	1.35	1.60	1.60	1.38	1.62	1.62	ns
DIFF_SSTL18_II_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns

Table 18 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

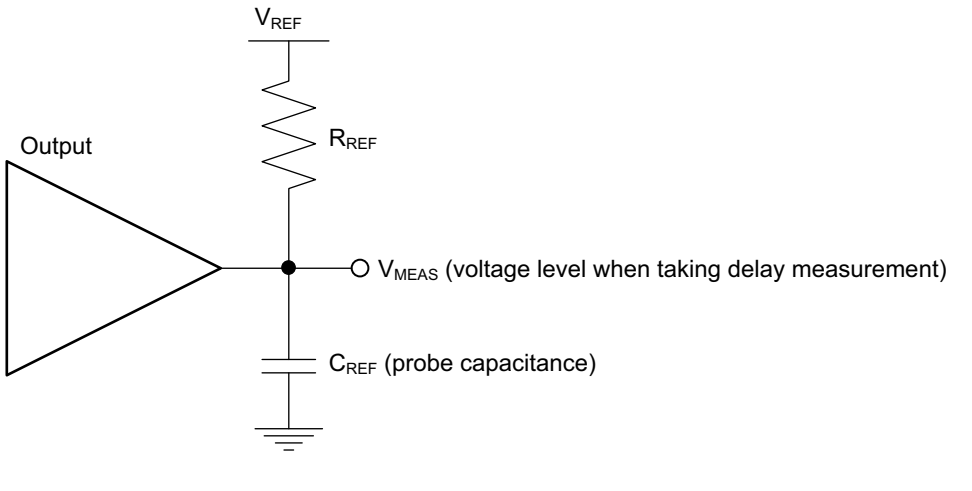

Figure 1: **Single-ended Test Setup**

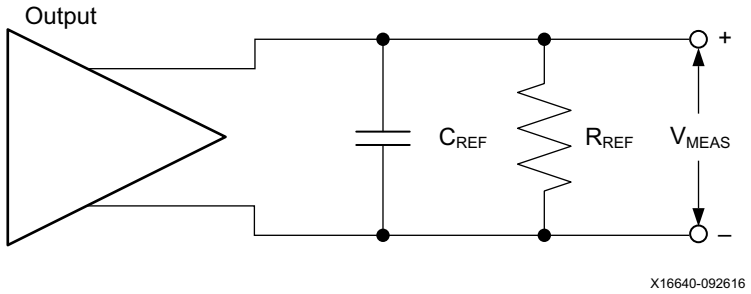

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 20.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Output Serializer/Deserializer Switching Characteristics

Table 24: **OSERDES Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold					
T_{OSDCK_D}/ T_{OSCKD_D}	D input setup/hold with respect to CLKDIV.	0.45/0.03	0.63/0.03	0.63/0.03	ns
T_{OSDCK_T}/ T_{OSCKD_T}	T input setup/hold with respect to CLK.	0.73/–0.13	0.88/–0.13	0.88/–0.13	ns
T_{OSDCK_T2}/ T_{OSCKD_T2}	T input setup/hold with respect to CLKDIV.	0.34/–0.13	0.39/–0.13	0.39/–0.13	ns
T_{OSCCK_OCE}/ T_{OSCKC_OCE}	OCE input setup/hold with respect to CLK.	0.34/0.58	0.51/0.58	0.51/0.58	ns
T_{OSCCK_S}	SR (reset) input setup with respect to CLKDIV.	0.52	0.85	0.85	ns
T_{OSCCK_TCE}/ T_{OSCKC_TCE}	TCE input setup/hold with respect to CLK.	0.34/0.01	0.51/0.01	0.51/0.01	ns
Sequential Delays					
T_{OSCKO_OQ}	Clock to out from CLK to OQ.	0.42	0.48	0.48	ns
T_{OSCKO_TQ}	Clock to out from CLK to TQ.	0.49	0.56	0.56	ns
Combinatorial					
T_{OSDO_TTQ}	T input to TQ out.	0.92	1.11	1.11	ns

Table 26: **IO_FIFO Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
IO_FIFO Clock to Out Delays					
T_{OFFCKO_DO}	RDCLK to Q outputs.	0.60	0.68	0.68	ns
T_{CKO_FLAGS}	Clock to IO_FIFO flags.	0.61	0.77	0.77	ns
Setup/Hold					
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK.	0.51/0.02	0.58/0.02	0.58/0.02	ns
T_{IFFCCK_WREN}/ T_{IFFCKC_WREN}	WREN to WRCLK.	0.47/–0.01	0.53/–0.01	0.53/–0.01	ns
T_{OFFCCK_RDEN}/ T_{OFFCKC_RDEN}	RDEN to RDCLK.	0.58/0.02	0.66/0.02	0.66/0.02	ns
Minimum Pulse Width					
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
Maximum Frequency					
F_{MAX}	RDCLK and WRCLK.	200.00	200.00	200.00	MHz

Block RAM and FIFO Switching Characteristics

Table 30: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Block RAM and FIFO Clock-to-Out Delays					
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (without output register).(1)(2)	2.13	2.46	2.46	ns, Max
	Clock CLK to DOUT output (with output register).(3)(4)	0.74	0.89	0.89	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register).(1)(2)	3.04	3.84	3.84	ns, Max
	Clock CLK to DOUT output with ECC (with output register).(3)(4)	0.81	0.94	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with cascade (without output register).(1)	2.88	3.30	3.30	ns, Max
	Clock CLK to DOUT output with cascade (with output register).(3)	1.28	1.46	1.46	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs.(5)	0.87	1.05	1.05	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs.(6)	1.02	1.15	1.15	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode.	0.85	0.94	0.94	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register).	2.81	3.55	3.55	ns, Max
	Clock CLK to BITERR (with output register).	0.76	0.89	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register).	0.88	1.07	1.07	ns, Max
	Clock CLK to RDADDR output with ECC (with output register).	0.93	1.08	1.08	ns, Max
Setup and Hold Times Before/After Clock CLK					
T_{RCCK_ADDRA}/ T_{RCKC_ADDRA}	ADDR inputs.(7)	0.49/0.33	0.57/0.36	0.57/0.36	ns, Min
$T_{RDCK\_DI\_WF\_NC}$/ $T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode.(8)	0.65/0.63	0.74/0.67	0.74/0.67	ns, Min
$T_{RDCK\_DI\_RF}$/ $T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode.(8)	0.22/0.34	0.25/0.41	0.25/0.41	ns, Min
$T_{RDCK\_DI\_ECC}$/ $T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode.(8)	0.55/0.46	0.63/0.50	0.63/0.50	ns, Min
$T_{RDCK\_DI\_ECCW}$/ $T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only.(8)	1.02/0.46	1.17/0.50	1.17/0.50	ns, Min

Table 30: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{RDCK\_DI\_ECC\_FIFO}$/ $T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode.(8)	1.15/0.59	1.32/0.64	1.32/0.64	ns, Min
$T_{RCCK\_INJECTBITERR}$/ $T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode.	0.64/0.37	0.74/0.40	0.74/0.40	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM enable (EN) input.	0.39/0.21	0.45/0.23	0.45/0.23	ns, Min
T_{RCCK_REGCE}/ T_{RCKC_REGCE}	CE input of output register.	0.29/0.15	0.36/0.16	0.36/0.16	ns, Min
T_{RCCK_RSTREG}/ T_{RCKC_RSTREG}	Synchronous RSTREG input.	0.32/0.07	0.35/0.07	0.35/0.07	ns, Min
T_{RCCK_RSTRAM}/ T_{RCKC_RSTRAM}	Synchronous RSTRAM input.	0.34/0.43	0.36/0.46	0.36/0.46	ns, Min
T_{RCCK_WEA}/T_{RCKC_WEA}	Write enable (WE) input (block RAM only).	0.48/0.19	0.54/0.20	0.54/0.20	ns, Min
T_{RCCK_WREN}/ T_{RCKC_WREN}	WREN FIFO inputs.	0.46/0.35	0.47/0.43	0.47/0.43	ns, Min
T_{RCCK_RDEN}/ T_{RCKC_RDEN}	RDEN FIFO inputs.	0.43/0.35	0.43/0.43	0.43/0.43	ns, Min
Reset Delays					
T_{RCO_FLAGS}	Reset RST to FIFO flags/pointers.(9)	0.98	1.10	1.10	ns, Max
T_{RREC_RST}/T_{RREM_RST}	FIFO reset recovery and removal timing.(10)	2.07/–0.81	2.37/–0.81	2.37/–0.81	ns, Max
Maximum Frequency					
$F_{MAX\_BRAM\_WF\_NC}$	Block RAM (write first and no change modes) when not in SDP RF mode.	460.83	388.20	388.20	MHz
$F_{MAX\_BRAM\_RF\_PERFORMANCE}$	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B.	460.83	388.20	388.20	MHz
$F_{MAX\_BRAM\_RF\_DELAYED\_WRITE}$	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses.	404.53	339.67	339.67	MHz
$F_{MAX\_CAS\_WF\_NC}$	Block RAM cascade (write first, no change mode) when cascade but not in RF mode.	418.59	345.78	345.78	MHz
$F_{MAX\_CAS\_RF\_PERFORMANCE}$	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled.	418.59	345.78	345.78	MHz

MMCM Switching Characteristics

Table 37: **MMCM Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
MMCM_F_{INMAX}	Maximum input clock frequency.	800.00	800.00	800.00	MHz
MMCM_F_{INMIN}	Minimum input clock frequency.	10.00	10.00	10.00	MHz
MMCM_$F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
MMCM_F_{INDUTY}	Allowable input duty cycle: 10—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: > 500 MHz.	45	45	45	%
MMCM_F_{MIN_PSCLK}	Minimum dynamic phase-shift clock frequency.	0.01	0.01	0.01	MHz
MMCM_F_{MAX_PSCLK}	Maximum dynamic phase-shift clock frequency.	500.00	450.00	450.00	MHz
MMCM_F_{VCOMIN}	Minimum MMCM VCO frequency.	600.00	600.00	600.00	MHz
MMCM_F_{VCOMAX}	Maximum MMCM VCO frequency.	1440.00	1200.00	1200.00	MHz
MMCM_$F_{BANDWIDTH}$	Low MMCM bandwidth at typical.(1)	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.(1)	4.00	4.00	4.00	MHz
MMCM_$T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.(2)	0.12	0.12	0.12	ns
MMCM_$T_{OUTJITTER}$	MMCM output jitter.	Note 3			
MMCM_$T_{OUTDUTY}$	MMCM output clock duty-cycle precision.(4)	0.20	0.20	0.20	ns
MMCM_$T_{LOCKMAX}$	MMCM maximum lock time.	100.00	100.00	100.00	µs
MMCM_F_{OUTMAX}	MMCM maximum output frequency.	800.00	800.00	800.00	MHz
MMCM_F_{OUTMIN}	MMCM minimum output frequency.(5)(6)	4.69	4.69	4.69	MHz
MMCM_$T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max			
MMCM_$RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	ns
MMCM_F_{PFDMAX}	Maximum frequency at the phase frequency detector.	500.00	450.00	450.00	MHz
MMCM_F_{PFDMIN}	Minimum frequency at the phase frequency detector.	10.00	10.00	10.00	MHz
MMCM_$T_{FBDELAY}$	Maximum delay in the feedback path.	3 ns Max or one CLKIN cycle			
MMCM Switching Characteristics Setup and Hold					
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and hold of phase-shift enable.	1.04/0.00	1.04/0.00	1.04/0.00	ns

Table 37: **MMCM Specification *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and hold of phase-shift increment/decrement.	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase shift clock-to-out of PSDONE.	0.68	0.81	0.81	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK					
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN setup/hold.	1.97/0.00	2.29/0.00	2.29/0.00	ns, Min
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY.	0.72	0.99	0.99	ns, Max
F_{DCK}	DCLK frequency.	200.00	200.00	200.00	MHz, Max

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the *Clocking Wizard* [Ref 8].
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.
6. When CLKOUT4_CASCADE = TRUE, MMCM_F_{OUTMIN} is 0.036 MHz.

PLL Switching Characteristics

Table 38: **PLL Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
PLL_F_{INMAX}	Maximum input clock frequency.	800.00	800.00	800.00	MHz
PLL_F_{INMIN}	Minimum input clock frequency.	19.00	19.00	19.00	MHz
PLL_$F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
PLL_F_{INDUTY}	Allowable input duty cycle: 19—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: >500 MHz.	45	45	45	%
PLL_F_{VCOMIN}	Minimum PLL VCO frequency.	800.00	800.00	800.00	MHz
PLL_F_{VCOMAX}	Maximum PLL VCO frequency.	1866.00	1600.00	1600.00	MHz

Table 38: **PLL Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
PLL_$F_{BANDWIDTH}$	Low PLL bandwidth at typical.	1.00	1.00	1.00	MHz
	High PLL bandwidth at typical.(1)	4.00	4.00	4.00	MHz
PLL_$T_{STATPHAOFFSET}$	Static phase offset of the PLL outputs.(2)	0.12	0.12	0.12	ns
PLL_$T_{OUTJITTER}$	PLL output jitter.	Note 3			
PLL_$T_{OUTDUTY}$	PLL output clock duty-cycle precision.(4)	0.20	0.20	0.20	ns
PLL_$T_{LOCKMAX}$	PLL maximum lock time.	100.00	100.00	100.00	µs
PLL_F_{OUTMAX}	PLL maximum output frequency.	800.00	800.00	800.00	MHz
PLL_F_{OUTMIN}	PLL minimum output frequency.(5)	6.25	6.25	6.25	MHz
PLL_$T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max			
PLL_$RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	ns
PLL_F_{PFDMAX}	Maximum frequency at the phase frequency detector.	500.00	450.00	450.00	MHz
PLL_F_{PFDMIN}	Minimum frequency at the phase frequency detector.	19.00	19.00	19.00	MHz
PLL_$T_{FBDELAY}$	Maximum delay in the feedback path.	3 ns Max or one CLKIN cycle			
Dynamic Reconfiguration Port (DRP) for PLL Before and After DCLK					
T_{PLLDCK_DADDR}/ T_{PLLCKD_DADDR}	Setup and hold of D address.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
T_{PLLDCK_DI}/ T_{PLLCKD_DI}	Setup and hold of D input.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
T_{PLLDCK_DEN}/ T_{PLLCKD_DEN}	Setup and hold of D enable.	1.97/0.00	2.29/0.00	2.29/0.00	ns, Min
T_{PLLDCK_DWE}/ T_{PLLCKD_DWE}	Setup and hold of D write enable.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
T_{PLLCKO_DRDY}	CLK to out of DRDY.	0.72	0.99	0.99	ns, Max
F_{DCK}	DCLK frequency.	200.00	200.00	200.00	MHz, Max

Notes:

1. The PLL does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any PLL outputs with identical phase.
3. Values for this parameter are available in the *Clocking Wizard* [Ref 8].
4. Includes global clock buffer.
5. Calculated as FVCO/128 assuming output duty cycle is 50%.

Device Pin-to-Pin Output Parameter Guidelines

Table 39: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Near Clock Region)[1]**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.						
T_{ICKOF}	Clock-capable clock input and OUTFF at pins/banks closest to the BUFGs *without* MMCM/PLL (near clock region).[2]	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	5.73	6.71	6.71	ns
		XC7S100	5.73	6.71	6.71	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	5.73	6.71	N/A	ns
		XA7S100	5.73	6.71	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 40: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Far Clock Region)[1]**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.						
$T_{ICKOFFAR}$	Clock-capable clock input and OUTFF at pins/banks farthest from the BUFGs *without* MMCM/PLL (far clock region).[2]	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	6.01	7.02	7.02	ns
		XC7S100	6.01	7.02	7.02	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	6.01	7.02	N/A	ns
		XA7S100	6.01	7.02	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 41: **Clock-Capable Clock Input to Output Delay With MMCM(1)**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* MMCM.						
$T_{ICKOFMMCMCC}$	Clock-capable clock input and OUTFF *with* MMCM.(2)	XC7S6	1.03	1.03	1.03	ns
		XC7S15	1.03	1.03	1.03	ns
		XC7S25	1.00	1.00	1.00	ns
		XC7S50	1.00	1.00	1.00	ns
		XC7S75	1.00	1.00	1.00	ns
		XC7S100	1.00	1.00	1.00	ns
		XA7S6	1.03	1.03	N/A	ns
		XA7S15	1.03	1.03	N/A	ns
		XA7S25	1.00	1.00	N/A	ns
		XA7S50	1.00	1.00	N/A	ns
		XA7S75	1.00	1.00	N/A	ns
		XA7S100	1.00	1.00	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 45: **Clock-Capable Clock Input Setup and Hold With MMCM**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard.(1)(2)						
$T_{PSMMCMCC}$/ $T_{PHMMCMCC}$	No delay clock-capable clock input and IFF(3) with MMCM.	XC7S6	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S15	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S25	2.69/–0.61	3.21/–0.61	3.21/–0.61	ns
		XC7S50	2.81/–0.62	3.35/–0.62	3.35/–0.62	ns
		XC7S75	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XC7S100	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XA7S6	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S15	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S25	2.69/–0.61	3.21/–0.61	N/A	ns
		XA7S50	2.81/–0.62	3.35/–0.62	N/A	ns
		XA7S75	2.81/–0.62	3.36/–0.62	N/A	ns
		XA7S100	2.81/–0.62	3.36/–0.62	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 46: **Clock-Capable Clock Input Setup and Hold With PLL**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Clock-Capable Clock Input Signal for SSTL15 Standard.(1)(2)						
$T_{PSPLLCC}$/ $T_{PHPLLCC}$	No delay clock-capable clock input and IFF(3) with PLL.	XC7S6	3.07/–0.17	3.69/–0.17	3.69/–0.17	ns
		XC7S15	3.07/–0.17	3.69/–0.17	3.69/–0.17	ns
		XC7S25	3.04/–0.19	3.64/–0.19	3.64/–0.19	ns
		XC7S50	3.15/–0.19	3.77/–0.19	3.77/–0.19	ns
		XC7S75	3.15/–0.19	3.78/–0.19	3.78/–0.19	ns
		XC7S100	3.15/–0.19	3.78/–0.19	3.78/–0.19	ns
		XA7S6	3.07/–0.17	3.69/–0.17	N/A	ns
		XA7S15	3.07/–0.17	3.69/–0.17	N/A	ns
		XA7S25	3.04/–0.19	3.64/–0.19	N/A	ns
		XA7S50	3.15/–0.19	3.77/–0.19	N/A	ns
		XA7S75	3.15/–0.19	3.78/–0.19	N/A	ns
		XA7S100	3.15/–0.19	3.78/–0.19	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 47: **Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Input Setup and Hold Time Relative to a Forwarded Clock Input Pin Using BUFIO for SSTL15 Standard.					
T_{PSCS}/T_{PHCS}	Setup and hold of I/O clock.	–0.38/1.46	–0.38/1.73	–0.38/1.76	ns